

Mau-Phon Houng

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of different temperatures to remove reduction gas on the photoluminescence properties of Eu-doped $\text{Li}_2(\text{Ba}_{1-x}\text{Sr}_x)\text{SiO}_4$ phosphors. <i>Luminescence</i> , 2021, 36, 20-27.	2.9	2
2	Enhancement of the properties of a Beta- Ga_2O_3 -based diode using fluorine-doped Ga_2O_3 films deposited by a liquid-phase method. <i>Functional Materials Letters</i> , 2021, 14, 2151036.	1.2	1
3	Fabrications of Hetero-Junction Schottky Diodes by Electrodeposition of Nano-Structured CuInSe_2 Materials Using Different Upper Electrodes. <i>Coatings</i> , 2020, 10, 266.	2.6	1
4	Synthesis of single-phase Au nanorods in an anodic aluminum oxide template with an optimized process for a highly sensitive and non-enzyme methyl mercaptan gas detector. <i>Microsystem Technologies</i> , 2018, 24, 4129-4136.	2.0	4
5	Electric Characteristic Enhancement of an AZO/Si Schottky Barrier Diode with Hydrogen Plasma Surface Treatment and Al_xO_x Guard Ring Structure. <i>Materials</i> , 2018, 11, 90.	2.9	2
6	Effect of Carbon Black Film on High-Frequency Power Absorption. <i>IEEE Microwave and Wireless Components Letters</i> , 2017, 27, 779-781.	3.2	3
7	The fabrication of high sensitivity gold nanorod H_2S gas sensors utilizing the highly uniform anodic aluminum oxide template. <i>AIP Advances</i> , 2016, 6, 125002.	1.3	3
8	High-Frequency Noise Absorption of AgFe_3O_4 Films on Microstrip Transmission Line. <i>IEEE Transactions on Magnetics</i> , 2015, 51, 1-4.	2.1	6
9	Effect of harmonic suppression on the dual-band bandpass filters using T-shaped and $\hat{\Gamma}$ -shaped transmission lines. <i>Microwave and Optical Technology Letters</i> , 2015, 57, 547-551.	1.4	3
10	Effect of sputtering power on the performance of p- $\text{Ni}_{1-x}\text{O}:\text{Li}/\text{n-Si}$ heterojunction solar cells. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 755-761.	2.2	0
11	Design of GSM/LTE multiband application for mobile phone antennas. <i>Electronics Letters</i> , 2015, 51, 1304-1306.	1.0	22
12	Nanomaterials for Nanooptoelectronics Device Applications. <i>Journal of Nanomaterials</i> , 2014, 2014, 1-1.	2.7	0
13	Study of working pressure on the optoelectrical properties of $\text{Al}:\text{Y}$ codoped ZnO thin-film deposited using DC magnetron sputtering for solar cell applications. <i>Applied Surface Science</i> , 2013, 280, 104-108.	6.1	28
14	Simple broadband anti-reflective coatings for superstrate-type silicon-based tandem cells. , 2012, , .		0
15	Effects of temperature and electrode distance on short-circuit current in amorphous silicon solar cells. , 2012, , .		1
16	Deposition of Preferred Orientation ZnO Films on the Lead-Free Ceramic Substrates and its Effects on the Properties of Surface Acoustic Wave Devices. <i>Journal of the American Ceramic Society</i> , 2012, 95, 2254-2259.	3.8	8
17	Improved Extraction Efficiency of Light-Emitting Diodes by Wet-Etching Modifying AZO Surface Roughness. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 362-364.	2.5	8
18	Investigation in Open Circuited Metal Lines Embedded in Defected Ground Structure and Its Applications to UWB Filters. <i>IEEE Microwave and Wireless Components Letters</i> , 2010, 20, 148-150.	3.2	43

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19	Enhancement of signal integrity for multi-module memory bus by particle swarm optimization. , 2010, , .		0
20	A 2.4 GHz highly linear image rejection low noise amplifier by using an active inductor. Microwave and Optical Technology Letters, 2009, 51, 1570-1573.	1.4	0
21	Harmonic suppression of bandpass filters using open-circuited stubs. Microwave and Optical Technology Letters, 2008, 50, 863-865.	1.4	3
22	Controllable reverse double U-shaped defected ground structure for bandpass filter with improved out-of-band performances. Microwave and Optical Technology Letters, 2008, 50, 3055-3057.	1.4	2
23	Modifying the improved light-output intensity of AlGaInP-based LEDs by nanoporous alumina. , 2008, , .		0
24	Minimized closed-loop high-selectivity dual-band filters using trisection stepped-impedance resonators. Microwave and Optical Technology Letters, 2007, 49, 219-221.	1.4	1
25	Package-induced cross-coupling effect on amplifier harmonic suppression. Microwave and Optical Technology Letters, 2007, 49, 332-336.	1.4	0
26	Simple method for a K-band SIW filter with dual-mode quasi-elliptic function response. Microwave and Optical Technology Letters, 2007, 49, 1246-1249.	1.4	16
27	Multilayer cross-coupled resonator bandpass filters fabricated on low temperature cofired ceramic substrates. Microwave and Optical Technology Letters, 2007, 49, 1977-1979.	1.4	1
28	A miniaturized bandpass filter fabricated on high dielectric constant ceramic substrates. Microwave and Optical Technology Letters, 2007, 49, 2087-2090.	1.4	4
29	A novel cross-shape DGS applied to design ultra-wide stopband low-pass filters. IEEE Microwave and Wireless Components Letters, 2006, 16, 252-254.	3.2	99
30	A novel compact ring dual-mode filter with adjustable second-passband for dual-band applications. IEEE Microwave and Wireless Components Letters, 2006, 16, 360-362.	3.2	116
31	A 12-36GHz PHEMT MMIC balanced frequency tripler. IEEE Microwave and Wireless Components Letters, 2006, 16, 19-21.	3.2	34
32	A single-supply Ku-band 1-W power amplifier MMIC with compact self-bias PHEMTs. IEEE Microwave and Wireless Components Letters, 2006, 16, 330-332.	3.2	8
33	Effect of bismuth addition on sintering behavior and microwave dielectric properties of zinc titanate ceramics. Journal of Electronic Materials, 2005, 34, 119-124.	2.2	9
34	A fully matched high linearity 2-W PHEMT MMIC power amplifier for 3.5 GHz applications. IEEE Microwave and Wireless Components Letters, 2005, 15, 667-669.	3.2	11
35	InGaP/InGaAs metal-oxide-semiconductor pseudomorphic high-electron-mobility transistor with a liquid-phase-oxidized InGaP as gate dielectric. IEEE Electron Device Letters, 2005, 26, 864-866.	3.9	23
36	Suppression of the burn-in effect in InGaP/GaAs heterojunction bipolar transistors by constant period of voltage stress. Journal of Applied Physics, 2004, 95, 2079-2083.	2.5	3

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37	Novel bandpass filter using tapered PBG cells. Microwave and Optical Technology Letters, 2004, 41, 66-68.	1.4	0
38	Characteristic impedance of a microstrip line using a DGS cell. Microwave and Optical Technology Letters, 2004, 43, 34-37.	1.4	3
39	A compact hairpin bandpass filter on high-permittivity dielectrics using a tape-casting technique. Microwave and Optical Technology Letters, 2004, 43, 164-166.	1.4	1
40	Improved Light-Output Power of GaN LEDs by Selective Region Activation. IEEE Photonics Technology Letters, 2004, 16, 1444-1446.	2.5	29
41	The microstructure investigation of flip-chip laser diode bonding on silicon substrate by using indium-gold solder. IEEE Transactions on Components and Packaging Technologies, 2003, 26, 635-641.	1.3	20
42	A planarized shallow-trench-isolation for GaAs devices fabrication using liquid phase chemical enhanced oxidation process. IEEE Electron Device Letters, 2002, 23, 237-239.	3.9	8
43	Orientation Dependence of Interface Inversion Asymmetry Effect on InGaAs/InP Quantum Wells. Physica Status Solidi (B): Basic Research, 2002, 231, 423-436.	1.5	1
44	Fabrication of depletion-mode GaAs MOSFET with a selective oxidation process by using metal as the mask. IEEE Electron Device Letters, 2001, 22, 2-4.	3.9	4
45	GaAs MOSFETs fabrication with a selective liquid phase oxidized gate. IEEE Transactions on Electron Devices, 2001, 48, 634-637.	3.0	12
46	Heat generation approximation in modulation-doped field-effect transistors by the energy relaxation between carriers and phonons. Journal of Applied Physics, 2000, 88, 2553-2559.	2.5	2
47	A GaAs MOSFET with a liquid phase oxidized gate. IEEE Electron Device Letters, 1999, 20, 18-20.	3.9	43
48	A DC model for asymmetric trapezoidal gate MOSFET's in strong inversion. IEEE Transactions on Electron Devices, 1998, 45, 1459-1467.	3.0	7
49	Humidity Effect on the High-T _c (Pb,Bi)SrCaCuO Superconductor. Journal of the American Ceramic Society, 1991, 74, 1710-1714.	3.8	4
50	Reliability issues on the novel surface acoustic wave notch filter. , 0, , .		0
51	The interface microstructure on the reliability of flip-chip laser diode bonding. , 0, , .		0
52	Factor considerations on the novel surface acoustic wave devices by using piezoelectric materials. , 0, , .		0
53	InGaP/InGaAs/GaAs metal-oxide-semiconductor pseudomorphic high electron mobility transistor with a liquid phase oxidized InGaP gate. , 0, , .		5
54	InAlAs/InGaAs Metamorphic High Electron Mobility Transistor with a Liquid Phase Oxidized InAlAs as Gate Dielectric. , 0, , .		0

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55	Liquid phase oxidation on InGaP and its application to InGaP/GaAs HBTs surface passivation. , 0, , .		6
56	InGaP PHEMT with a Liquid Phase Oxidized InGaP as Gate Dielectric. , 0, , .		1